

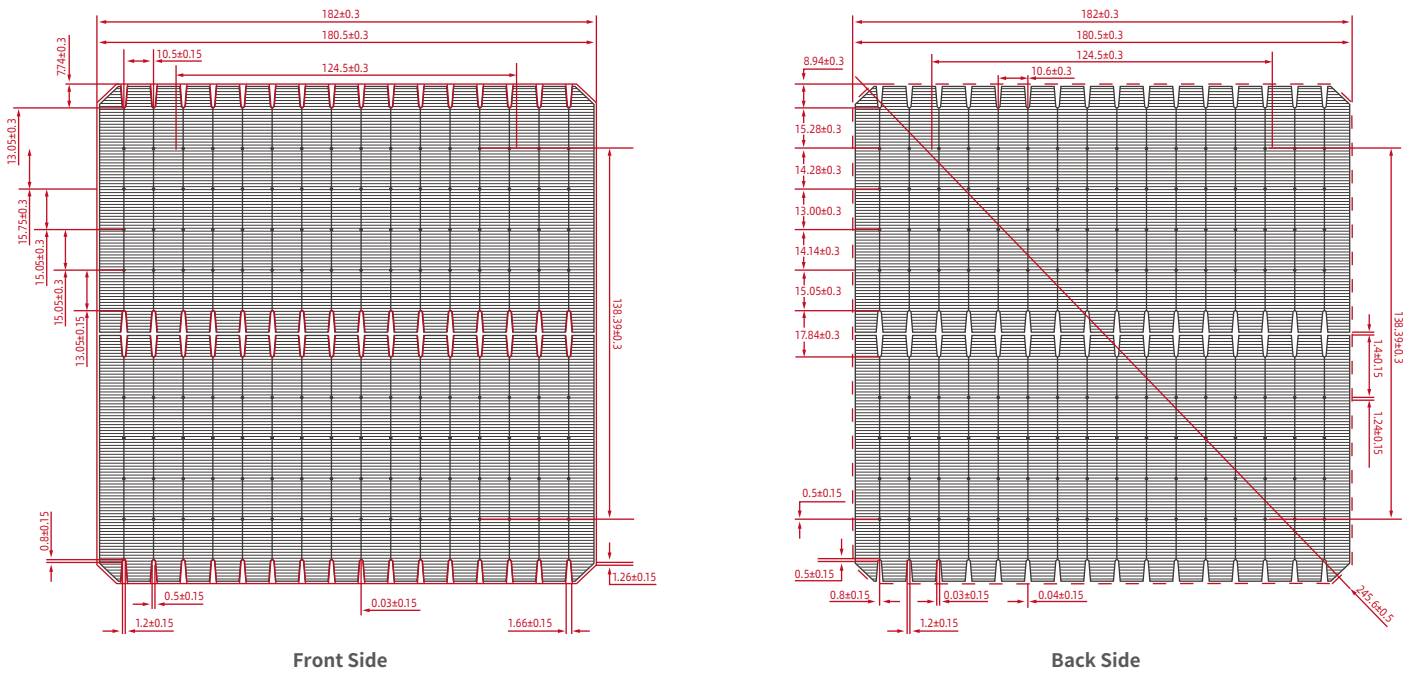
JS182N16

Superior
performance

Product Specification

Item	Wafer
Materia	Silicon
Crystal growth mode	CZ CzochralskiMethod
Conductive type	N-type
Resistivity	0.3-2.1ohm/cm2
Minority carrier lifetime	≥800μs
Interstitial oxygen content	≤13ptma
Substitution carbon content	≤1ptma
Wafer Type	Mono
Wafer Size	182*182±0.3mm
Chamfer length	245.6±0.3mm
Angle	90±0.2°
Cell Thickness	140μm±14μm

Solar Cell Structure



Electrical performance

Eff(%)	Pmpp(W)	Vmpp(V)	I _{mp} (A)	U _{oc} (V)	I _{sc} (A)	FF(%)
25.1	8.30	0.625	13.279	0.713	13.766	84.50
25.0	8.27	0.624	13.252	0.712	13.748	84.47
24.9	8.23	0.623	13.212	0.711	13.741	84.31
24.8	8.20	0.622	13.185	0.709	13.729	84.22
24.7	8.16	0.622	13.119	0.709	13.730	83.81
24.6	8.13	0.621	13.098	0.709	13.716	83.69
24.5	8.10	0.620	13.062	0.707	13.708	83.54
24.4	8.06	0.620	13.007	0.707	13.705	83.23
24.3	8.02	0.618	12.985	0.706	13.694	82.92
24.2	7.99	0.617	12.951	0.705	13.689	82.86
24.1	7.97	0.617	12.921	0.705	13.646	82.85
24.0	7.93	0.616	12.875	0.704	13.624	82.68
23.9	7.89	0.615	12.831	0.704	13.575	82.57
23.8	7.86	0.615	12.781	0.705	13.541	82.34
23.7	7.82	0.614	12.735	0.705	13.506	82.12

Standard test conditions: AM 1.5, 1000W/m², 25°C